

FORM PTO-1449 U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket Number
5308-390

Serial No.
10/815,293

LIST OF DOCUMENTS CITED BY APPLICANT

(Use several sheets if necessary)

Applicants:

Donofrio

Filing Date

April 1, 2004

Group

2814
2829

U. S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
AC	1.	3,954,534	05/04/76	Scifres et al.	156	7	
	2.	4,545,366	10/08/85	O'Neill	126	440	
	3.	4,672,949	06/16/87	O'Neill	126	700	
	4.	4,711,972	12/08/87	O'Neill	136	246	
	5.	4,719,904	01/19/88	O'Neill	126	650	
	6.	4,918,497	04/17/90	Edmond	357	17	
	7.	4,966,862	10/30/90	Edmond	437	100	
	8.	5,027,168	06/25/91	Edmond	357	17	
	9.	5,210,051	05/11/93	Carter, Jr.	437	107	
	10.	5,338,944	08/16/94	Edmond et al.	257	76	
	11.	5,393,993	02/28/95	Edmond et al.	257	77	
	12.	5,416,342	05/16/95	Edmond et al.	257	76	
	13.	5,498,297	03/12/96	O'Neill et al.	136	246	
	14.	5,505,789	04/09/96	Fraas et al.	136	246	
	15.	5,523,589	06/04/96	Edmond et al.	257	77	
	16.	5,604,135	02/18/97	Edmond et al.	437	22	
	17.	5,631,190	05/20/97	Negley	438	33	
	18.	5,739,554	04/14/98	Edmond et al.	257	103	
	19.	5,779,924	07/14/98	Krames et al.	216	24	
	20.	5,793,062	08/11/98	Kish, Jr. et al.	257	98	
	21.	5,912,477	06/15/99	Negley	257	95	
	22.	6,031,179	02/29/00	O'Neill	136	246	
	23.	6,075,200	06/13/00	O'Neill	136	246	
	24.	6,111,190	08/29/00	O'Neill	136	246	
AC	25.	6,120,600	09/19/00	Edmond et al.	117	89	

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Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Alonso Chambliss

5/27/06

FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)					Attorney Docket Number 5308-390		Serial No. 10/815,293	
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					Filing Date April 1, 2004			Group 2829 2814
AC	26.	6,177,688	01/23/01	Linthicum et al.	257	77		
AC	27.	6,187,606	02/13/01	Edmond et al.	438	46		
AC	28.	6,201,262	03/13/01	Edmond et al.	257	77		
Duplicate	29.	6,410,942	06/25/02	Thibeault et al.	257	88		
AC	30.	2002/0123164	09/05/02	Slater, Jr. et al.	438	39		
AC	31.	2003/0006418	01/09/03	Emerson et al.	257	79		
Duplicate	32.	6,657,236	12/02/03	Thibeault et al.	257	98		
AC	33.	2004/0056260	03/25/04	Slater, Jr. et al.	257	79		
FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation Yes No	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)								
AC	34.	Boehlen et al., "Laser Micro-Machining of High Density Optical Structures on Large Substrates," Exitech Ltd, Oxford Industrial Park, 10 pages.						
	35.	Craford, <i>Overview of Device Issues in High-Brightness Light-Emitting Diodes</i> , Chapter 2, <i>High Brightness Light Emitting Diodes: Semiconductors and Semimetals</i> , Vol. 48, Stringfellow et al. ed., Academic Press, 1997, pp. 47-63						
	36.	Köck et al., "Strongly Directional Emission from AlGaAs/GaAs Light Emitting Diodes," <i>Applied Physics Letter</i> , 57(22): 2327-2329 (November 26, 1990)						
	37.	Krames et. al., "High Power Truncated-Inverted-Pyramid (Al _x Ga _{1-x}) _{0.5} In _{0.5} P/GaP Light-Emitting Diodes Exhibiting >50% External Quantum Efficiency," <i>Applied Physics Letters</i> , 75(16): 2365-2367 (October 18, 1999)						
	38.	Shnitzer et al., "30% External Quantum Efficiency from Surface Textured, Thin-Film Light Emitting Diodes," <i>Applied Physics Letters</i> , 63(16): 2174-2176 (October 18, 1993)						
AC	39.	Shnitzer et al., "Ultrahigh Spontaneous Emission Quantum Efficiency, 99.7% Internally and 72% Externally, from AlGaAs/GaAs/AlGaAs Double Heterostructures," <i>Applied Physics Letters</i> , 62(2): 131-133 (January 11, 1993)						

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